



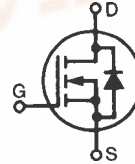
Advance Technical Information

Trench Gate Power MOSFET

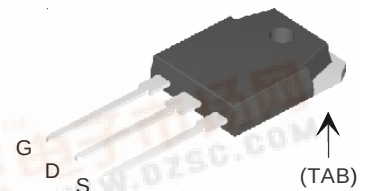
IXTQ 180N055T
IXTA 180N055T
IXTP 180N055T

$V_{DSS} = 55 \text{ V}$
 $I_{D25} = 180 \text{ A}$
 $R_{DS(on)} = 4.0 \text{ m}\Omega$

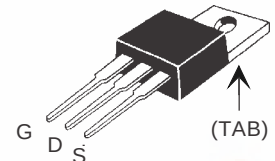
N-Channel Enhancement Mode



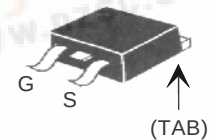
TO-3P (IXTQ)



TO-220 (IXTP)



TO-263 (IXTA)



G = Gate
S = Source

D = Drain
TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	55	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	55	V
V_{GSM}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	180	A
I_{DRMS}	External lead current limit	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	600	A
I_{AR}	$T_C = 25^\circ\text{C}$	75	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 10 \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	360	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s Maximum tab temperature for soldering TO-263 package for 10s	300 260	$^\circ\text{C}$ $^\circ\text{C}$
M_d	Mounting torque (TO-3P / TO-220)	1.13/10	Nm/lb.in.
Weight	TO-3P TO-220 TO-263	5.5 4 3	g g g

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	55		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			1 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 50 \text{ A}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$	3.3		4.0 $\text{m}\Omega$

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect

Advantages

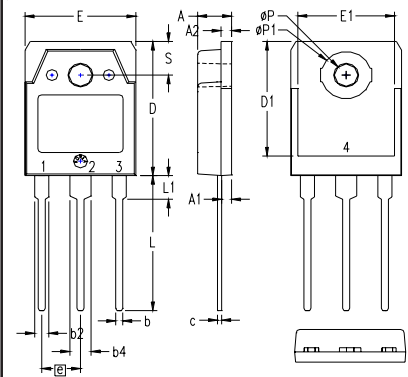
- Easy to mount
- Space savings
- High power density



Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10 V; I _D = 50 A, pulse test	70	90	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5800	pF
C_{oss}			1190	pF
C_{rss}			138	pF
$t_{d(on)}$	V _{GS} = 10 V, V _{DS} = 40 V, I _D = 40 A R _G = 5 Ω (External)		37	ns
t_r			61	ns
$t_{d(off)}$			65	ns
t_f			36	ns
$Q_{g(on)}$	V _{GS} = 10 V, V _{DS} = 30 V, I _D = 90 A		160	nC
Q_{gs}			46	nC
Q_{gd}			47	nC
R_{thJC}				0.42 K/W
R_{thCK}	(TO-3P) (TO-220)		0.21 0.25	K/W K/W

Source-Drain Diode		Characteristic Values (T _j = 25°C, unless otherwise specified)		
Symbol	Test Conditions	Min.	typ.	Max.
I_s	V _{GS} = 0 V			180 A
I_{SM}	Repetitive			600 A
V_{SD}	I _F = 50 A, V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.2 V
t_{rr}	I _F = 25 A -di/dt = 100 A/μs		80	ns
Q_{RM}	V _R = 25 V		0.4	μC

TO-3P (IXTQ) Outline

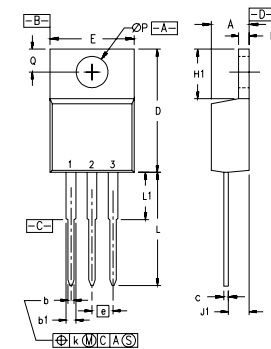


- 1 - GATE
2 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)
4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

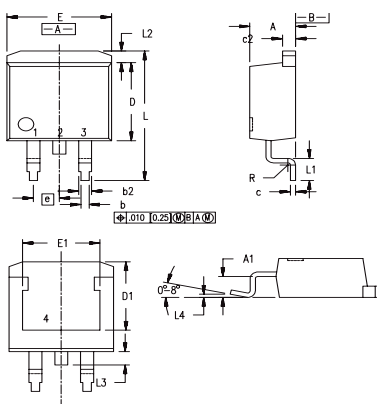
TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain

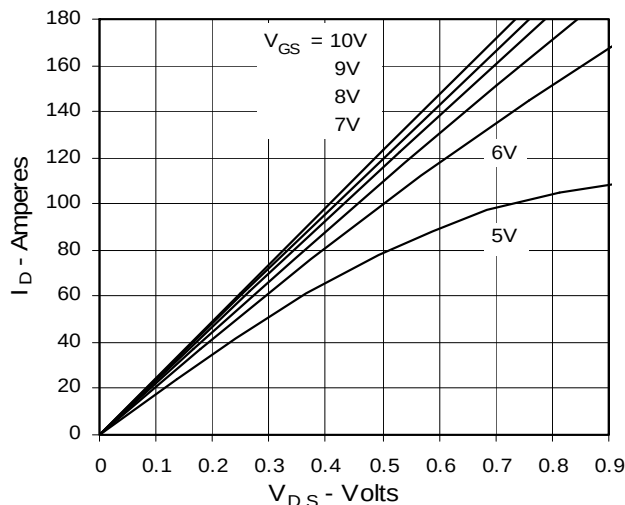
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
øP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-263 (IXTA) Outline

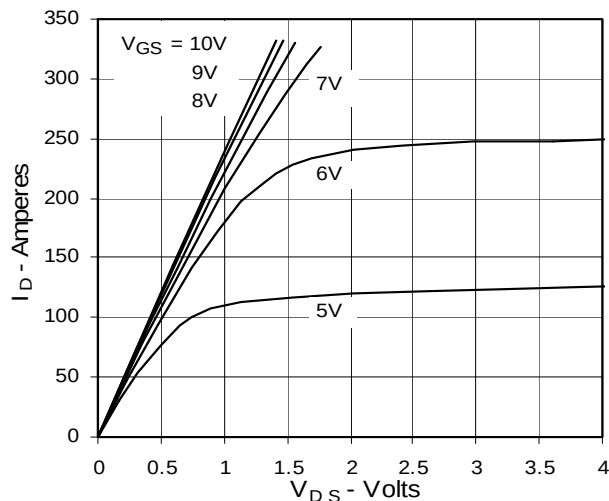


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

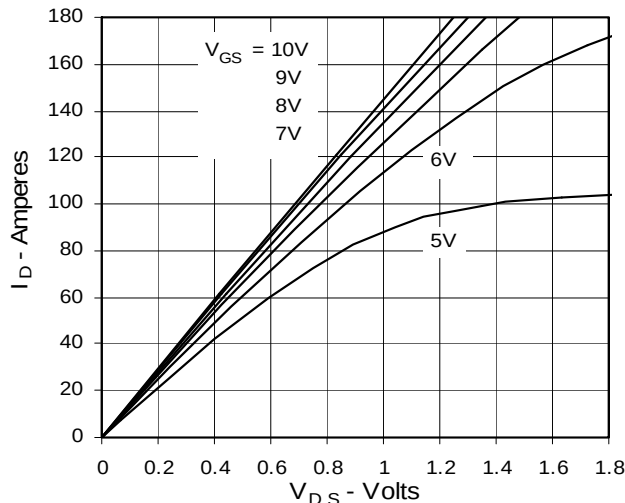
**Fig. 1. Output Characteristics
@ 25°C**



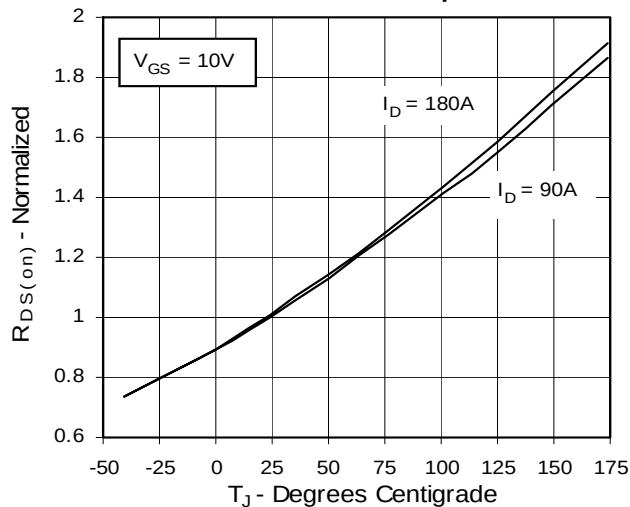
**Fig. 2. Extended Output Characteristics
@ 25°C**



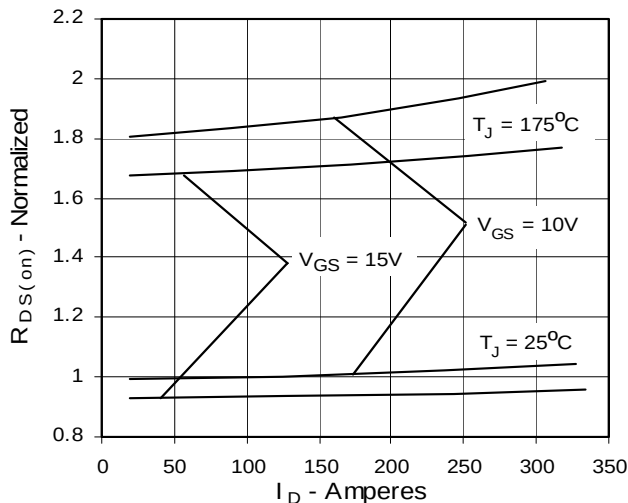
**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Drain Current**



**Fig. 6. Drain Current vs. Case
Temperature**

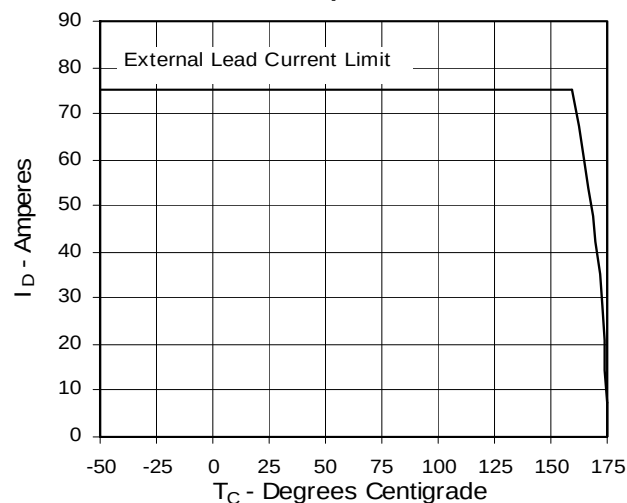


Fig. 7. Input Admittance

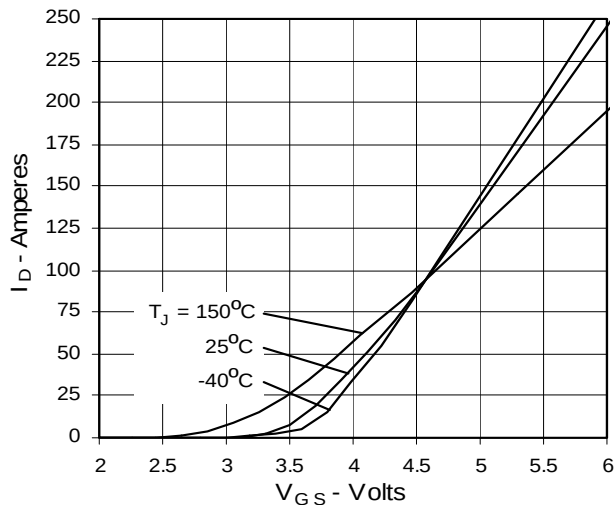


Fig. 8. Transconductance

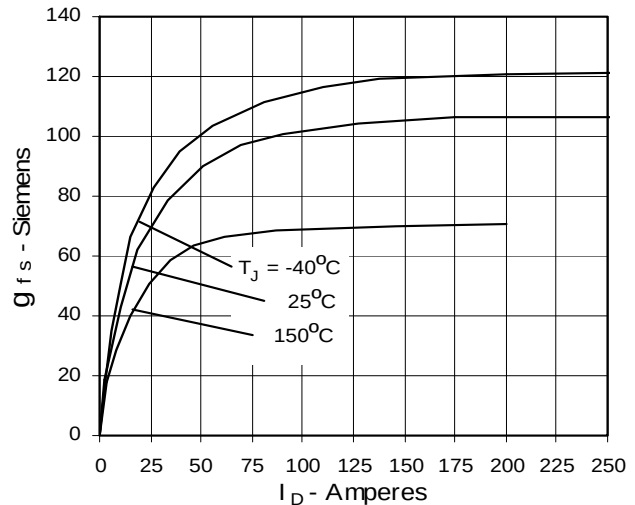


Fig. 9. Source Current vs. Source-To-Drain Voltage

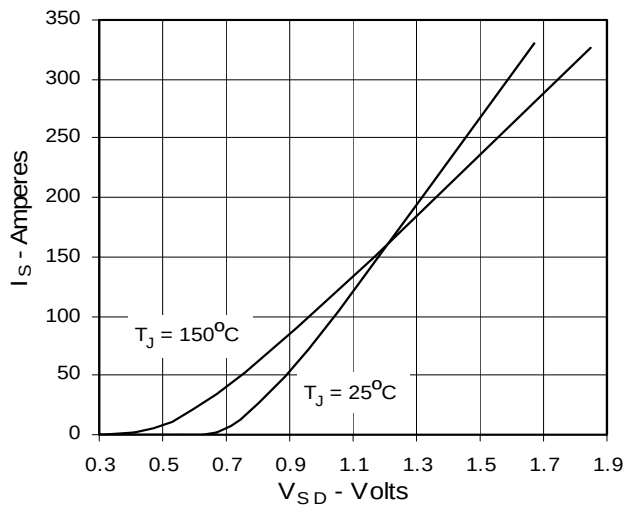


Fig. 10. Gate Charge

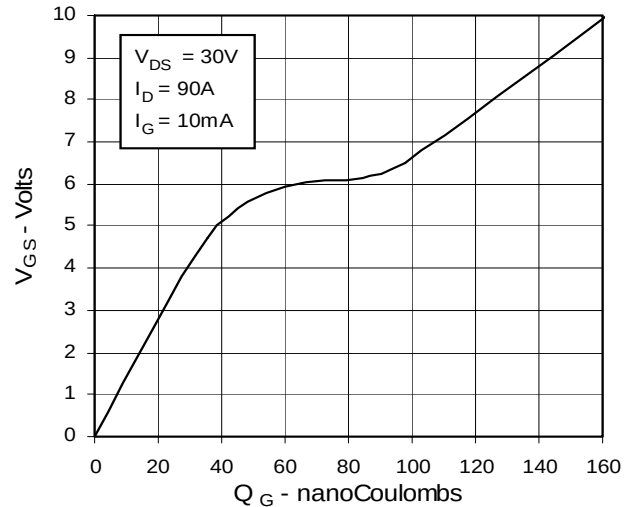


Fig. 11. Capacitance

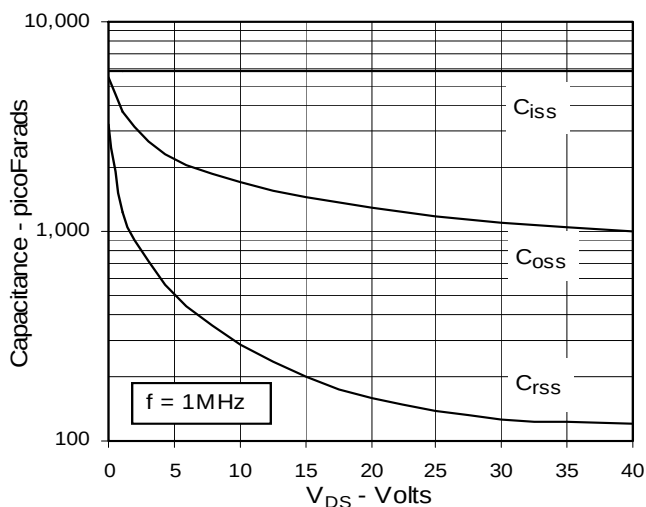


Fig. 12. Forward-Bias Safe Operating Area

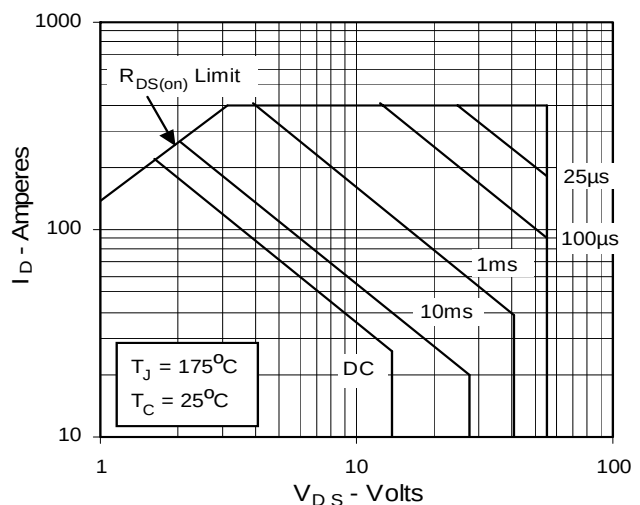


Fig. 13. Maximum Transient Thermal Resistance

